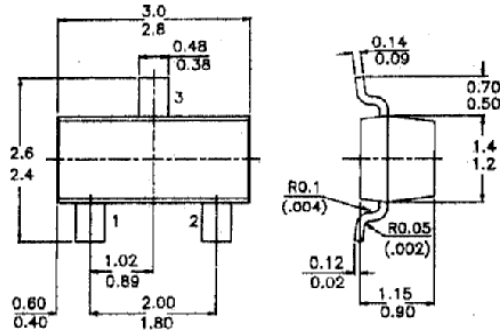
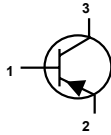


## PNP Silicon Planar Epitaxial Transistors

Pin configuration:  
1. BASE  
2. EMITTER  
3. COLLECTOR



**SOT-23 SMD Package**

Unit: mm

### Absolute Maximum Ratings (Ta = 25 °C unless specified otherwise)

DESCRIPTION	SYMBOL	CMBT2907	CMBT2907A	UNITS
Collector Emitter Voltage	$-V_{CEO}$	40	60	V
Collector Base Voltage	$-V_{CBO}$	60	60	
Emitter Base Voltage	$-V_{EBO}$	5.0	5.0	
Collector Current	$-I_C$	600		mA
Power dissipation up to Tamb = 25 °C	$P_{tot}$	250		mW
Storage Temperature	$T_{stg}$	-55 to +150		°C
Junction Temperature	$T_j$	150		
DC Current Gain $-V_{CE} = 10V$ $-I_C = 500mA$	$h_{FE}$	> 30	> 50	
Turn-off switching time $-I_{Con} = 150 mA$ ; $-I_{BOn} = I_{Boff} = 15 mA$	$t_{off}$	< 100		ns
Transition frequency at f = 100 MHz $-I_C = 50 mA$ ; $-V_{CE} = 20 V$	$f_T$	> 200		MHz

### Thermal Characteristics

Junction to Ambient in free air	$R_{th(j-a)}$	500	K/W
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### Electrical Characteristics (at Ta=25 °C unless otherwise specified)

DESCRIPTION	SYMBOL	CONDITIONS	CMBT2907	CMBT2907A	UNITS
Collector Cut Off Current	$-I_{CBO}$	$I_E = 0, -V_{CB} = 50V$	< 20	< 10	nA
	$-I_{CBO}$	$I_E = 0, -V_{CB} = 50V, T_j = 125^\circ C$	< 20	< 10	uA
	$-I_{CEX}$	$-V_{EB} = 0.5V, -V_{CE} = 30V$	< 50		
Base Current w/reverse biased emitter junction	$-I_{BEX}$	$-V_{EB} = 3V, -V_{CE} = 30V$	< 50		nA
Saturation Voltages	$-V_{CE(Sat)}$	$-I_C = 150mA, -I_B = 15mA$	< 0.4		V
	$-V_{BE(Sat)}$		< 1.3		
	$-V_{CE(Sat)}$	$-I_C = 500mA, -I_B = 50mA$	< 1.6		
	$-V_{BE(Sat)}$		< 2.6		
Collector-base breakdown voltage	$-V_{(BR)CBO}$	Open emitter; $-I_C = 10uA, I_E = 0$	> 60		
Collector-emitter breakdown voltage	$-V_{(BR)CEO}$	Open base; $-I_C = 10mA, I_B = 0$	> 40	> 60	
Emitter-base breakdown voltage	$-V_{(BR)EBO}$	Open collector; $-I_E = 10uA, I_C = 0$	> 5.0		

